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[1] H. Tomori *et al.*, Appl. Phys. Expr. **4**, 075102 (2011).

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| Fig.1: The trap is connected to electrodes with the rates ΓN and Γ±. A magnetic field **B** defines the trap spin quantization axis OZ’ at an angle Θ to the magnetization orientation OZ in the ferromagnet. | Fig.4: Current as a function of Θ, for p=1, ΓN/ΓF = 10, ωL/ΓF = 1, ΓF T1 = 10, and several values of T2/T1. |
|  |  |
| Fig.2: Current in units of eΓN as a function of Θ for p=1, ΓN/ΓF = 10, ωL/ΓF = 1, and several values of T2=T1. | Fig.5 Normalized current as a function of the position x relative to silicon, for p=1, ΓN=Γ0 exp(-x/d) , ΓF=Γ0 exp(-(d-x)/d), T2=T1, ωLT2 = Γ0T2 =10,  |
|  |  |
| Fig.3: Current as a function of Θ, for ΓN/ΓF = 10, ωL/ΓF = 1, ΓF T1 = ΓF T1 = 10, and several values of p. | Fig.6: Magnetoresistance signal as a function of the perpendicular magnetic field **B** for several T2/T1, for p=0.8 and ΓF T1 = 10. The field **B**0 is parallel to the magnetization in the ferromagnet. |